

IN THE CLAIMS:

The following is a listing of the claims as pending in the application that replaces all previously filed claim listings:

Please amend claims 1 and 3 as follows:

1. (Currently Amended) A palladium-plated lead finishing structure characterized in that Pd or a Pd alloy is plated to a thickness of not more than 0.3 μm only on the surface of a plurality of the external connection terminals of a semiconductor part using copper or a copper alloy-based material, without interposing any underlying layer or any intermediate metal layer between said material and said Pd- or Pd alloy plated later, and the surfaces of inner leads are plated with silver.

2. (Original) The palladium-plated lead finishing structure according to claim 1, wherein Au or an Au alloy is plated to a thickness of not more than 0.1 μm on the top of said Pd or Pd alloy layer.

3. (Currently Amended) A palladium-plated lead finishing structure characterized in that Pd or a Pd alloy is plated to a thickness of not more than 0.3 μm only on the surfaces of a plurality of the external connection terminals of a semiconductor part using iron or an iron-nickel-based material, without interposing any underlying layer or any intermediate metal layer between said material and said Pd- or Pd alloy-plated layer, and the surfaces of inner leads are plated with silver.

4. (Original) The palladium-plated lead finishing structure according to claim 3, wherein Au or an Au alloy is plated to a thickness of not more than 0.1 μm on the top of said Pd or Pd alloy layer.

5. (Withdrawn) A method of producing a semiconductor device characterized by plating Pd or a Pd alloy, to a thickness of not larger than 0.3 μm , on the surfaces of the external connection terminals of a semiconductor part using copper or a copper alloy-based material, without interposing any underlying layer or any intermediate metal layer between the surfaces of said material of the external connection terminals and said Pd- or Pd alloy-plated layer after at least the steps of mounting a semiconductor chip by die attachment, wire bonding and resin molding.

6. (Withdrawn) A method of producing a semiconductor device characterized by plating Pd or a Pd alloy to a thickness of not more than 0.3 μm on the surfaces of the external connection terminals of a semiconductor par using iron or an iron-nickel-based material, without interposing any underlying layer or any intermediate metal layer between the surfaces of said material of the external connection terminals and said Pd- or Pd alloy-plated layer after at least the steps of mounting a semiconductor chip by die attachment, wire bonding and resin molding.